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Fairchild Semiconductor 2N6518BU

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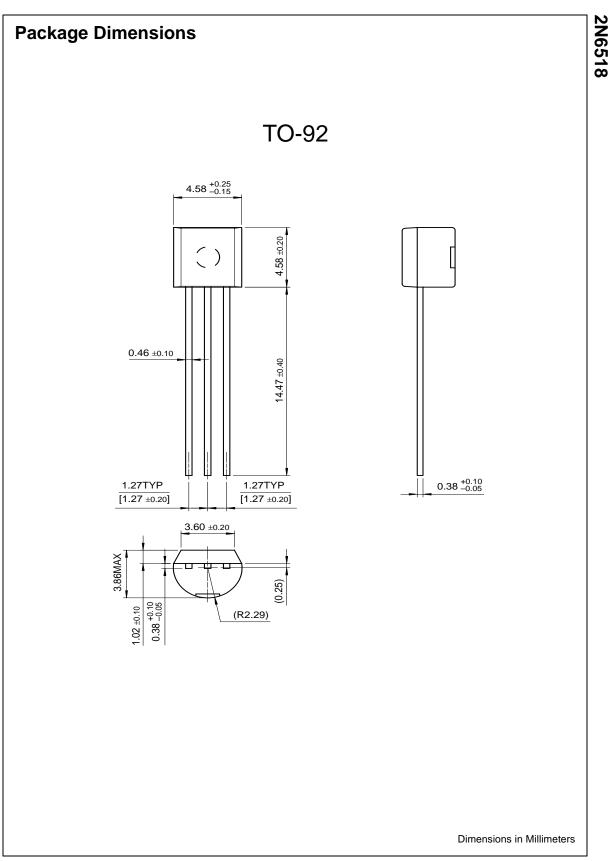


EMICC	INDUCTOR [®]					
	2	N6518				
Collector- Collector Complem	Ditage Transistor Emitter Voltage: V _{CEO} = -250V Dissipation: P _C (max)=625mW ent to 2N6515 Pitaxial Silicon Transis	tor 1. Emi	T ter 2. Bas	O-92 e 3. Colle	ector	
	e Maximum Ratings T _a =25°C					
Symbo		er	Value	L	Inits	
V _{CBO}	Collector-Base Voltage		-250		V	
V _{CEO}	Collector-Emitter Voltage				V	
V _{EBO}	Emitter-Base Voltage		-5		V	
l _C	Collector Current		-500		mA	
I _B	Base Current			-250 m		
P _C	Collector Power Dissipation		625		mW	
-	Derate above 25°C		5			
T _J Junction Temperature			150		°C	
T _{STG}	Storago Tomporaturo		55 150		°C	
Refer to 2N652	Storage Temperature 20 for graphs		55 ~ 150		°C	
Refer to 2N652	20 for graphs al Characteristics T _a =25°C unle	ss otherwise noted		Max	-	
Refer to 2N652 Electric Symbol	20 for graphs al Characteristics T _a =25°C unle Parameter	ss otherwise noted Test Condition	55 ~ 150 Min. -250	Max.	-	
Refer to 2N652 Electric Symbol BV _{CBO}	20 for graphs al Characteristics T _a =25°C unle	ss otherwise noted Test Condition I _C = -100μA, I _E =0	Min.	Max.	Units	
Refer to 2N652 Electric Symbol BV _{CBO} BV _{CEO}	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage	ss otherwise noted Test Condition I_{C} = -100 μ A, I_{E} =0 I_{C} = -1mA, I_{B} =0	Min. -250	Max.	Units V	
Refer to 2N652 Electric Symbol BV _{CBO} BV _{CEO} BV _{EBO}	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage	ss otherwise noted Test Condition I _C = -100μA, I _E =0	Min. -250 -250	Max.	Units V V	
Refer to 2N652 Electric Symbol BV _{CBO} BV _{CEO} BV _{EBO} I _{CBO}	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage	ss otherwise noted Test Condition $I_C= -100\mu A, I_E=0$ $I_C= -1mA, I_B=0$ $I_E= -10\mu A, I_C=0$	Min. -250 -250		Units V V	
Refer to 2N652 Symbol BV _{CBO} BV _{CEO} BV _{EBO} ICBO IEBO	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current	ss otherwise noted Test Condition $I_{C}=-100\mu$ A, $I_{E}=0$ $I_{C}=-1mA$, $I_{B}=0$ $I_{E}=-10\mu$ A, $I_{C}=0$ $V_{CB}=-150V$, $I_{E}=0$ $V_{EB}=-4V$, $I_{C}=0$ $V_{CE}=-10V$, $I_{C}=-10mA$ $V_{CE}=-10V$, $I_{C}=-30mA$ $V_{CE}=-10V$, $I_{C}=-50mA$	Min. -250 -250	-50	Units V V V nA	
Refer to 2N652 Symbol BV _{CBO} BV _{CEO} BV _{EBO} I _{CBO} I _{EBO} h _{FE}	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current	$\begin{tabular}{ c c c c c } \hline $$ therwise noted $$ $$ therwise noted $$ $$ $$ I_C=-100\mu A, I_E=0 $$ $$ $$ $$ I_C=-10\mu A, I_C=0 $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$$	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -50 50	-50 -50 300 220 -0.30 -0.35 -0.50	Units V V V V nA nA V V V V V V V V V V V V V	
Refer to 2N652 Symbol BV _{CBO} BV _{CBO} BV _{EBO} I _{CBO} I _{CBO} h _{FE} V _{CE} (sat)	20 for graphs al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain	$\begin{tabular}{ c c c c c } \hline $$ therwise noted $$ $$ therwise noted $$ $$ I_C= -100\mu A, I_E=0 $$ $$ I_C= -10\mu A, I_C=0 $$ $$ $$ I_E= -10\mu A, I_C=0 $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$$	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -50 -50 -50 -45	-50 -50 300 220 -0.30 -0.35	Units V V V V nA nA V V V	
Refer to 2N652 Electric Symbol BV _{CBO} BV _{CEO}	al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage	$\begin{tabular}{ c c c c c } \hline $$ therwise noted $$ $$ therwise noted $$ $$ I_C= -100\muA, I_E=0 $$ $$ I_C= -10\muA, I_C=0 $$ $$ $$ I_C= -10\muA, I_C=0 $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$$	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -50 -50 -50 -45	-50 -50 220 -0.30 -0.35 -0.50 -1 -0.75 -0.85	Units V V nA nA V	
Bymbol BV _{CBO} BV _{CEO} BV _{CBO} ICBO IcBO IcBO VCE (sat)	al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{tabular}{ c c c c c } \hline $$ the set $	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -5 -5 -5	-50 -50 220 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90	Units V V nA nA V	
Refer to 2N652 Symbol BV _{CBO} BV _{CEO} BV _{CBO} ICBO ICBO ICBO VBE VCE (sat) VBE (sat) VBE (on)	al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage	Test Condition I _C = -100µA, I _E =0 I _C = -10µA, I _C =0 V _C B= -150V, I _E =0 V _C B= -4V, I _C =0 V _C E= -10V, I _C = -10MA V _C E= -10V, I _C = -10MA V _C E= -10V, I _C = -10MA V _C E= -10V, I _C = -100MA V _C E= -10V, I _C = -50mA V _C E= -10W, I _C = -100mA I _C = -20mA, I _B = -2mA I _C = -30mA, I _B = -3mA I _C = -10mA, I _B = -1mA I _C = -20mA, I _B = -2mA I _C = -30mA, I _B = -3mA V _C E= -10V, I _C = -100mA	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -5 -5 -5	-50 -50 220 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2	Units V V V V N N N N V V V V V V V V V V V	
Refer to 2N652 Symbol BV _{CBO} BV _{CEO} BV _{EBO} IcBO IcBO VBE (sat) VBE (sat) VBE (on) fT Cob	al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage * Current Gain Bandwidth Product	Test Condition I _C = -100µA, I _E =0 I _C = -1mA, I _B =0 I _E = -10µA, I _C =0 V _{CB} = -150V, I _E =0 V _{CE} = -10V, I _C = -1mA V _{CE} = -10V, I _C = -10mA V _{CE} = -10V, I _C = -30mA V _{CE} = -10V, I _C = -30mA V _{CE} = -10V, I _C = -100mA I _C = -10mA, I _B = -1mA I _C = -20mA, I _B = -2mA I _C = -30mA, I _B = -3mA I _C = -20mA, I _B = -3mA I _C = -30mA, I _B = -3mA I _C = -30mA, I _B = -3mA I _C = -10V, I _C = -100mA	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -5 -5 -5	-50 -50 -50 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2 200	Units V V N nA nA N V V V	
Refer to 2N652 Symbol BV _{CBO} BV _{CEO} BV _{EBO} IcBO IcBO VBE VCE (sat) VBE (sat) VBE (on) fT	al Characteristics T _a =25°C unle Parameter * Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Base-Emitter On Voltage * Current Gain Bandwidth Product Output Capacitance	Test Condition I _C = -100µA, I _E =0 I _C = -1mA, I _B =0 I _E = -10µA, I _C =0 V _{CB} = -150V, I _E =0 V _{CE} = -10V, I _C = -10mA V _{CE} = -10V, I _C = -10mA V _{CE} = -10V, I _C = -30mA V _{CE} = -10V, I _C = -100mA V _{CE} = -10V, I _C = -100mA I _C = -10mA, I _B = -1mA I _C = -20mA, I _B = -2mA I _C = -30mA, I _B = -3mA I _C = -20mA, I _B = -3mA I _C = -30mA, I _B = -3mA I _C = -20mA, I _B = -2mA I _C = -20mA, I _B = -3mA I _C = -20mA, I _B = -3mA I _C = -20V, I _C = -100mA V _{CE} = -20V, I _C = -10mA, f=20MH; V _{CE} = -20V, I _C = -10mA, f=20MH;	Min. -250 -250 -5 -5 -5 -5 -5 -5 -5 -5 -5 -5	-50 -50 -50 220 -0.30 -0.35 -0.50 -1 -0.75 -0.85 -0.90 -2 200 6	Units V V N nA nA N V PF	

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